TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA2008ANG

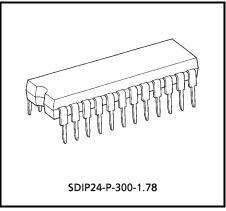
5V AM / FM 1 Chip Tuner IC (for digital tuning system)

The TA2008ANG is the AM / FM 1 chip tuner IC, which is designed for radio cassette players and music centers. This is suitable for digital tuning system applications.

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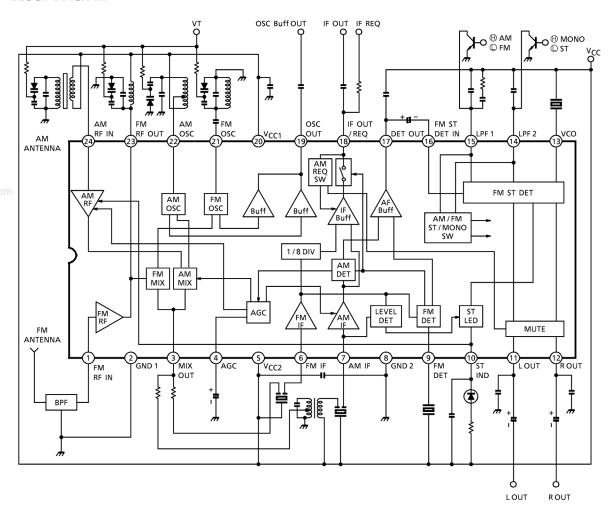
Features

- Suitable for combination with digital tuning system which is included IF counter.
- One terminal type AM / FM IF count output (auto stop signal) for IF counter of digital tuning system.
 - FM: 1.3375MHz (1 / 8 dividing)
 - AM: 450kHz
- Built-in mute circuit for IF count output.
- For adopting ceramic discriminator and ceramic resonator, it is not necessary to adjust the FM quad detector circuit and FM stereo detector vco circuit.
- Built-in one terminal type AM / FM local oscillator buffer output for digital tuning system applications.
- Operating supply voltage range: VCC = 3.5~14V (Ta = 25°C)



Weight: 1.2g (typ.)

BLOCK DIAGRAM



Explanation Of Terminals

Pin	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
No.	Onaradionalio	menal olloat	AM	FM	
1	FM-RF in	FM-RF OUT 23 GND1 2	0	0.8	
2	GND1 (GND for RF stage)	_	0	0	
3	Mix out	VCC1 20 AM MIX FM MIX GND1 2 3	0.3	0.8	
4	AGC	V _{CC2} (5)	1.2	0.9	
5	V _{CC2} (V _{CC} for IF / FM ST DET stage)	_	5.0	5.0	
6	FM IF in	VCC2 (5) (3) (6) (8) (7) (7) (7) (7) (7) (7) (7) (7) (7) (7	5.0	5.0	

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
INO.			AM	FM	
7	AM IF in	VCC2 5 G	5.0	5.0	
8	GND2 (GND for if / FM ST DET stage)	_	0	0	
9	QUAD (FM QUAD. Detector)	V _{CC2} (S) (9) (9) (1) (1) (1) (1) (1) (1) (1) (1) (1) (1	4.1	3.6	
10	St ind • Stereo LED terminal • Offset voltage cancel for AM RF amp.	19kHz AM RF Amp	4.2	_	
11 12	L-out (L-ch output) R-out (R-ch output)	11/12 GND2 8	1.35	1.35	

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Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
INO.			AM	FM	
13	VCO	V _{CC2} (5) (3) (3) (3) (4) (4) (4) (4) (4) (4) (4) (4) (4) (4	5.0	4.1	
14	LPF2 • LPF terminal for synchronous detector. • VCO stop terminal V ₁₄ = GND → VCO stop	GND2 8	5.0	3.4	
15	LPF1 • LPF terminal for phase detector • Bias terminal for AM / FM SW circuit $V_{15} = \text{GND} \rightarrow \text{AM}$ $V_{15} = \text{open} \rightarrow \text{FM}$	GND2 8	0	2.8	
16	FM ST DET in	(16) W W W W W W W W W W W W W W W W W W W	1.4	1.4	

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Pin No.	Characteristic	Internal Circuit	(at no	tage (V) signal) FM	
17	DET out	VCC2 S AM OFFM FM 17 B LOW-FM, HIGH-AM B LOW-AM, HIGH-FM	AM 1.4	1.4	
18	IF out / REQ V_{18} = GND \rightarrow IF out	5 VCC2	4.0	4.0	
19	OSC out	AM OSC FM OSC 2 GND1	4.0	4.0	
20	V _{CC1} (V _{CC} for RF stage)	_	5.0	5.0	
21	FM OSC	VCC1 20 TO THE TOTAL TOT	5.0	5.0	

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Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)		
NO.	0.		AM	FM	
22	AM OSC	② VCC1 ② GND1	5.0	5.0	
23	FM RF out	cf. pin (1)	5.0	5.0	
24	AM RF in	VCC1 20 AGC 24 GND2 2	5.0	5.0	

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Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V _{CC}	15	V
LED current	I _{LED}	10	mA
LED voltage	V _{LED}	15	V
Power dissipation	P _D *	1200	mW
Operating temperature	T _{opr}	-25~75	°C
Storage temperature	T _{stg}	-55~150	°C

^{* :} Derated above Ta = 25°C in the proportion of 9.6mW / °C

Electrical Characteristics

Unless Otherwise Specified, Ta = 25°C, V_{cc} = 5V, SW8: Off, F / E: f = 98MHz, f_m = 1kHz FM IF: f = 10.7MHz, Δf = ±22.5kHz, f_m = 1kHz ΔM : f = 1MHz, MOD = 30%, f_m = 1kHz FM ST DET: f_m = 1kHz

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit	
Supply current		I _{CC (FM)}	- V _{in} = 0, FM mode		_	27	36	mA	
Оцрр	ry current	I _{CC (AM)}	I	V _{in} = 0. AM mode	_	18	25	IIIA	
./E	Input limiting voltage	V _{in} (lim)		–3dB limiting with respect to V _{OD} level at Vin = 60dBμV EMF	_	11	_	dBµV EMF	
L	Local OSC buffer output voltage	V _{OSC} (buff) FM	_	f _{OSC} = 108.7MHz	90	180	_	mV _{rms}	
	Input limiting voltage	V _{in} (lim.) IF	_	–3dB limiting with respect to V _{OD} level at V _{in} = 80dBμV EMF	40	45	50	dBµV EMF	
	Recovered output voltage V _{OD} - V _{in} = 80dBμV EMF		50	75	100	mV _{rms}			
	Signal to noise ratio S/N — $V_{in} = 80 dB \mu V EMF$		_	70	_	dB			
	Total harmonic distortion THD — V _{in} = 80dBµV EMF		V _{in} = 80dBμV EMF		0.3		%		
FM IF	AM rejection ratio	AMR	— V _{in} = 80dBμV EMF		_	50	_	dB	
	SD output sensitivity	D output sensitivity V_{SD} — $V_{SD} = V_{CC} - 0.1V$		53	58	63	dBµV EMF		
	IF count output frequency	f1 / 8 IF (FM)		V _{in} = 80dBμV EMF, SW8: On	1.3373	1.3375	1.3377	MHz	
	IF count output voltage	V1 / 8 IF (FM)	ı	V _{in} = 80dBμV EMF,SW8: On	350	500	_	mV _{p-p}	
	IF count output sensitivity	IF sens (FM)	_	SW8: On	49	54	59	dBµV EMF	

Characteristic			Symbol	Test Cir- cuit	Test Condi	tion	Min.	Тур.	Max.	Unit
	Gain	Gain		_	V _{in} = 26dBµV EMF		20	45	80	mV_{rms}
	Recovered o	utput	V _{OD}	_	V _{in} = 60dBµV EMF		45	65	90	mV _{rms}
	Signal to noi	se ratio	S/N	_	V _{in} = 60dBµV EMF		_	42	_	dB
ΑM	Total harmor distortion	nic	THD	_	V _{in} = 60dBµV EMF		_	1.0	_	%
	Local OSC boutput voltage		V _{OSC} (buff) AM	_	f _{OSC} = 1.45MHz		90	150	_	mV _{rms}
	IF count outp	out	V _{IF} (AM)	_	V _{in} = 60dBµV EMF,	SW8: On,	350	500	_	mV _{p-p}
	IF count outp	out	IF sens (AM)	_	SW8: On		35	40	45	dBµV EMF
Din /	17) output rook	otonoo	R17		FM mode		_	0.75	_	kΩ
PIII (Pin (17) output resistance		KI/	_	AM mode	_	15.5	_	K12	
	Input resistar	nce	R _{IN}	_			_	24	_	kΩ
	Output resist	Output resistance		_			_	5	_	kΩ
	Max. Composite signal input voltage		V _{in max} (stereo)	_	L + R = 90%, P = 10%, SW4: LPF on f _m = 1kHz, THD = 3%		_	800	_	mV _{rms}
	Separation			_	L + R = 180mV _{rms} P = 20mV _{rms} SW4: LPF on	f _m = 100Hz	_	42	_	dB
			Sep.			f _m = 1kHz	35	42	_	
				$f_{m} = 10kHz$	f _m = 10kHz	_	42	_		
DET	Total harmonic	Monaural	THD (monaural)		V _{in} = 200mV _{rms}		_	0.1	_	%
FM St DE	distortion	Stereo	THD (stereo)	_	L + R = 180mV _{rms} , P = 20mV _{rms} , SW4: LPF on,		_	0.1	_	70
ᇤ	Voltage gain		G _V	_	V _{in} = 200mV _{rms}		-2	0	2	dB
	Channel bala	ance	C. B.	_	V _{in} = 200mV _{rms}		-2	0	2	dB
	Stereo LED	On	V _{L (ON)}		Pilot input		_	8	15	mV _{rms}
	sensitivity	Off	V _{L (OFF)}		T not input		2	6	1	iii v rms
	Stereo LED I	Stereo LED hysteresis		_	To LED turn off from LED turn on		_	2	_	mV _{rms}
	Capture rang	je	C. R.		P = 15mV _{rms}			±1.3		%
	Signal to noi	se ratio	S/N	_	V _{in} = 200mV _{rms}			80		dB
	Muting attenuation		MUTE	_	V _{in} = 200mV _{rms}	_	80	_	dB	

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3 3KU ±#_€ ROUT CB2426F29 LOUT 500kუ **1** 1 280.0 ᅜ ∃≒890.0 FM ST DET IN ዏ⋆ 330bt ₹₽.@ 3300pF B 6800pF CDA10.7MG45 Şo DET GND 2 Şφ 02261330 TA2008ANG 100KT MM SFU450B ∃µ, 10.0 FM IF 98C **1** 1 € £ 0 . 0 န္ဂါ နွ ğÇ 1≒, E60.0 FIII—€ 9 Puo Š å 🤄 \$ે ≅& 100kO 2.1kD **≨**5€ છે. કેલ્ 100kg o ₹ GND 1 2707 2705 \frac{\frac{1}{8}}{8} \sqrt{\frac{1}{8}} \cdot \frac{1}{8} ΰïs

TA2008ANG-10

Coil Data

Cail Na	Test	L	Co	0		Tu	rns		Wire	Deference
Coil No.	Freq.	(µH)	(pF)	Q_0	1–2	2–3	1–3	3–6	(mmφ)	Reference
L1 FM RF	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
L1 FM OSC	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
T1 AM mix	455kHz		180	48↑	47	111	158	4–6 20	0.06 UEW	(T): A7LCS-12064N
T2 AM OSC	796kHz	268		125	15	89			0.06 UEW	(S): 2157–2239–213A (T): A7BRS–11998Y

(S): Sumida electric co., Itd.

T2: AM OSC

(T): Toko co., Itd.

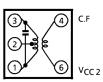
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 $\begin{array}{c} \mathsf{L}_1 \ : \ \mathsf{FM} \ \mathsf{RF} \\ \mathsf{L}_2 \ : \ \mathsf{FM} \ \mathsf{OSC} \end{array}$

3

T1 : AM MIX

GND 2

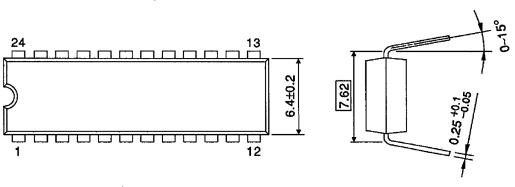




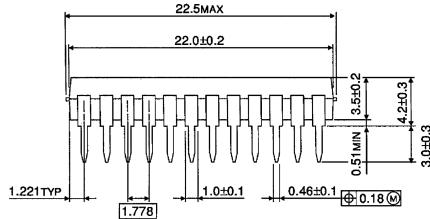
Unit: mm

Package Dimensions

SDIP24-P-300-1.78



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Weight: 1.2g (typ.)

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About solderability, following conditions were confirmed

- Solderability
 - (1) Use of Sn-37Pb solder Bath
 - · solder bath temperature = 230°C
 - · dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux
 - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
 - · solder bath temperature = 245°C
 - · dipping time = 5 seconds
 - · the number of times = once
 - · use of R-type flux